Supplementary Materials for

Doping with Metal-Organic Framework Materials (ZIF-8)

on perovskite photoconductive detector for improving

stability and photoresponsivity

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Figs. S1~S7 and Table S1



Fig. S1. Relationship between ZIF-8 (5g/mL) addition concentration and photoresponsivity

5 1	1 2	1 0
Addition ratio	Photocurrent	Photoresponsivity
	А	A/W
0%	1.927*10-7	4.033*10-2
2.5%	2.431*10-7	5.087*10-2
5%	2.731*10-7	5.714*10-7
7.5%	2.824*10-7	5.909*10-7
10%	3.327*10-7	6.961*10-7
12.5%	2.901*10-7	6.071*10-7
15%	2.250*10-7	4.708*10-7
17.5%	2.245*10-7	4.698*10-7

Table S1 Summary of photoresponsivity of devices with different doping concentrations



Fig. S2. The cross-sectional SEM images of MAPbI₃ perovskite with ZIF-8



Fig. S3. The SEM images of mixed crystal



Fig. S4. (a) The perovskite ink without ZIF-8. (b) The perovskite ink with ZIF-8 and needle-shaped crystal. (c) The needle-shaped crystals removed from perovskite ink for 2min without any treatment.



Fig. S5. Optical bandgap estimated for MAPbI₃ and MAPbI₃-Z8.



Fig. S6. XPS spectra of MAPbI3 and MAPbI3-Z8 films.



Fig. S8. Logarithm I–V characteristics of photodetectors with MAPbI₃ and MAPbI₃-Z8 layer in the dark state condition